

being made by deformation of the pads.

7. A structure according to claim 6, wherein

said bumps of said semiconductor device are pressed on said pads of said board,

a portion in which each of said bumps and a corresponding one of said pads are in contact with each other is heated, wherein pressure of said bumps against said pads reaches a predetermined value which plastically deforms said pads before a temperature of said insulating adhesive to which heat is supplied in step (b) reaches temperature at which said insulating adhesive is hardened, wherein

said insulating adhesive has heating characteristics by which liquidity of said insulating adhesive is produced by an initial heating stage and said insulating adhesive is gradually hardened with increasing temperature.

8. A structure according to claim 6, wherein

a head heated at a temperature at which said insulating adhesive is hardened presses said semiconductor device on said board so that each of said bumps is pressed on a corresponding one of said pads, wherein pressure of said bumps against said pads reaches a predetermined value which plastically deforms said pads before a temperature of said insulating adhesive to which heat is supplied from said head reaches temperature at which said insulating adhesive is hardened,

said head is released from pressing said semiconductor device after said insulating adhesive is completely hardened, wherein

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said insulating adhesive has heating characteristics by which liquidity of said insulating adhesive is produced by an initial heating stage and said insulating adhesive is gradually hardened with increasing temperature.

9. A structure according to claim 6, wherein  
said bumps of said semiconductor device are pressed on said pads of said board so as to plastically deform the pads before the insulating adhesive is hardened, and  
pressing of said bumps is stopped after the insulating adhesive is hardened.

10. A structure according to claim 6, wherein  
said bumps of said semiconductor device are pressed on said pads of said board so as to plastically deform the pads before the insulating adhesive is hardened, by a head heated at a temperature at which the insulating adhesive is hardened, and  
the head is released from pressing the semiconductor device after the insulating adhesive is hardened.

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11. A structure according to claim 6, wherein  
a member between said semiconductor device and said board is provided, said member having a thermal characteristic of delaying transmission of heat, and  
a heat treated at a temperature at which said insulating adhesive is hardened presses said semiconductor device on said board so that each of said bumps is pressed on a corresponding one

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of said pads, wherein pressure of said bumps against said pads reaches a predetermined value which plastically deforms said pads before a temperature of said insulating adhesive to which heat is supplied from said head reaches temperature at which said insulating adhesive is hardened.

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